EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	10/709999	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/08/25 06:47
L2	0	2005/0020076	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/08/25 06:48
L3	1	"20050020076"	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/08/25 06:51
L4	1	"20040043526"	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/08/25 06:53
L5	3233325	"20040223267" A1	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/08/25 06:53
L6	2	"20040223267"	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/08/25 06:55
L7	1	"20040084400"	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/08/25 07:01
L8	6	("20020036876"|"20020142192"|"5346841"|"6083794"|"6452764"|"6759263").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/08/25 07:01
L9	53	("20020036876"|"20020142192"|"5346841"|"6083794"|"6452764"|"6759263")	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/08/25 07:03

L10	40	("0009616"|"0048127"|"20030198113"|"20030198113"|"0181056"|"20040001350"|"20040001350"|"20040043526"|"20040051522"|"20040051522"|"20040084400"|"20040252559"|"20040252559"|"20040253437"|"20040253437"|"20050020076"|"20050050399"|"20050050399"|"20050079647"|"20050079647"|"20050079683"|"20050079683"|"20050087519"|"20050087519"|"20050088875"|"20050088875"|"20050102581"|"20050102581"|"20050127418"|"20050127418"|"20050151552"|"20050151552"|"20050185458"|"20050185458"|"4619872"|"5792569"|"5946228"|"6034887"|"6072718"|"6104633"|"6299991"|"6299991"|"6333067"|"6333067"|"6385082"|"6385082"|"6452764"|"6452764"|"6538919"|"6538919"|"6660568"|"6660568"|"6784091"|"6784091"|"6812141"|"6812141"|"6365419"|"6495275"|"6548849").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/08/25 07:03
L11	362	("0009616"|"0048127"|"20030198113"|"20030198113"|"0181056"|"20040001350"|"20040001350"|"20040043526"|"20040051522"|"20040051522"|"20040084400"|"20040252559"|"20040252559"|"20040253437"|"20040253437"|"20050020076"|"20050050399"|"20050050399"|"20050079647"|"20050079647"|"20050079683"|"20050079683"|"20050087519"|"20050087519"|"20050088875"|"20050088875"|"20050102581"|"20050102581"|"20050127418"|"20050127418"|"20050151552"|"20050151552"|"20050185458"|"20050185458"|"4619872"|"5792569"|"5946228"|"6034887"|"6072718"|"6104633"|"6299991"|"6299991"|"6333067"|"6333067"|"6385082"|"6385082"|"6452764"|"6452764"|"6538919"|"6538919"|"6660568"|"6660568"|"6784091"|"6784091"|"6812141"|"6812141"|"6365419"|"6495275"|"6548849")	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/08/25 07:04
L12	402	11 or 9	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/08/25 07:04
L13	23	12 and ((mask hardmask) near3 (metal conductive))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/08/25 07:19

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L14	259	("MTJ" magnetic ajd tunnel adj junction) and ((mask hardmask) near3 (metal conductive)) with (conductive near3 line wiring wire)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/08/25 07:22
L15	0	12 and ((pinned free) near3 layer) with ("MTJ" magnetic ajd tunnel adj junction) and ((mask hardmask) near3 (metal conductive)) with (conductive near3 line wiring wire)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/08/25 07:23
L16	34	14 and ((pinned free) near3 layer) with ("MTJ" magnetic ajd tunnel adj junction)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/08/25 07:24
S40	1435	(magnetic adj tunnel adj junction "MTJ" "MRAM" (magnetoresistive magneto adj resistive) near3 memory) with (free pinned) near3 (layer film)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/17 12:24
S41	894	S40 and barrier with (free pinned) near3 (layer film)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/17 12:25
S42	75	S41 and (mask$3 hardmask$3) same barrier with (free pinned) near3 (layer film)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/17 13:34
S43	1435	(magnetic adj tunnel adj junction "MTJ" "MRAM" (magnetoresistive magneto adj resistive) near3 memory) with (free pinned) near3 (layer film)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/17 13:35
S44	894	S43 and barrier with (free pinned) near3 (layer film)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/17 14:10
S45	75	S44 and (mask$3 hardmask$3) same barrier with (free pinned) near3 (layer film)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/17 13:35
S46	3	S45 and (free) near3 (layer film) with (inacti$4)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/17 13:37
S47	5	S44 and free with inact$4	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/17 13:58
S48	580	S44 and free with resist$4	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/17 13:58

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S49	1022	S43 and (barrier nonmagnetic insulator) with (free pinned) near3 (layer film)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/17 14:15
S50	10	S49 and (free) near3 (layer film) with convers$4	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/17 14:11
S51	82	S43 and (barrier nonmagnetic insulator) with (free pinned) near3 (layer film) same (mask$3 hardmask$3)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/17 14:29
S52	1	10/709999	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/17 14:23
S53	318	S43 and (barrier nonmagnetic insulator) with (free pinned) near3 (layer film) and (mask$3 hardmask$3)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/17 14:30
S54	281	S53 and (free) near3 (layer film) and (mask$3 hardmask$3 hard nwae3 mask$3)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/17 14:32
S55	281	S53 and (free) near3 (layer film) and (mask$3 hardmask$3 hard near3 mask$3)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/18 08:19
S56	38	S55 and (free mask$3 hardmask$3 hard near3 mask$3) with (oxidation oxidizing oxioxidization oxidized)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/18 10:31
S57	2	10/283348	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/08/25 06:35
S58	2	((free) near3 (layer film)) with (mask$3 hardmask$3 hard near3 mask$3) with anodi$4	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/18 08:21
S59	0	((free adj layer)) with (mask$3 hardmask$3 hard near3 mask$3) with (anodi$4 anodization)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/18 08:21
S60	5	((free adj layer)) with (anodi$4 anodization)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/18 08:22

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S61	240	sputtering with (method process) and (plasma near3 bombardment) with (method process)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/18 10:33
S62	76	sputtering with (method process) same (plasma near3 bombardment) with (method process)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/18 10:34
S63	88	sputtering with (method process) and (plasma near3 bombardment) with (method process) and (planarization planarizing planar$3)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/18 10:37
S64	29	sputtering near3 (method process) and (plasma near3 bombardment) near3 (method process) and (planarization planarizing planar$3)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/18 10:41
S65	9	sputtering near3 (method process) and (plasma near3 bombardment) near3 (method process) same (planarization planarizing planar$3)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/18 10:44
S66	9	(sputtering near3 (method process) and (plasma near3 bombardment) near3 (method process)) same (planarization planarizing planar$3)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/18 10:44
S67	1	(sputtering near3 (method process) and (plasma near3 bombardment) near3 (method process)) with (planarization planarizing planar$3)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	ON	2006/04/18 10:45